

Features

- Low on-resistance
- JESD22-A114-B ESD rating of class 2 per human body model
- High-speed switching
- Drive circuits can be simple
- Parallel use is easy
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

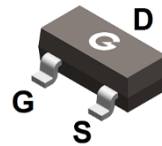
HF

Typical Applications

- N-channel enhancement mode effect transistor
- Switching application

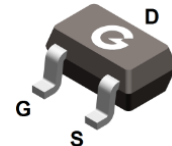
Mechanical Data

- Case: SOT-23, SOT-323, SOT-523, DFN1006-3, SOT-723
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



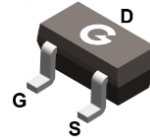
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SOT-23



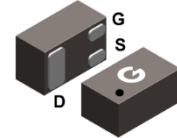
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SOT-323



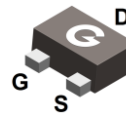
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SOT-523



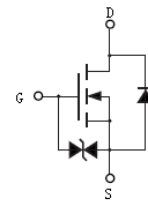
T2N5003L

DFN1006-3



T2N5003M

SOT-723



Ordering Information

Part Number	Package	Shipping	Marking Code
T2N5003	SOT-23	3000pcs / Tape & Reel	5003
T2N5003W	SOT-323	3000pcs / Tape & Reel	5003
T2N5003T	SOT-523	3000pcs / Tape & Reel	53
T2N5003L	DFN1006-3	10000pcs / Tape & Reel	53
T2N5003M	SOT-723	10000pcs / Tape & Reel	5003

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	50	V
Gate -Source Voltage		V _{GSS}	±20	V
Continuous Drain Current *1		I _D	300	mA
Pulsed Drain Current (t _p = 10μs) *1		I _{DM}	2000	mA
Power Dissipation *1	SOT-23	P _D	0.35	W
	SOT-323		0.25	
	SOT-523		0.15	
	DFN1006-3		0.15	
	SOT-723		0.15	

Thermal Characteristics

Parameter		Symbol	Limits	Unit
Thermal Resistance Junction to Ambient Air *1	SOT-23	R _{θJA}	357	°C/W
	SOT-323		500	
	SOT-523		833	
	DFN1006-3		833	
	SOT-723		833	
Thermal Resistance Junction to Lead *1	SOT-23	R _{θJL}	234	°C/W
	SOT-323		313	
	SOT-523		521	
	DFN1006-3		521	
	SOT-723		521	
Thermal Resistance Junction to Case *1	SOT-23	R _{θJC}	195	°C/W
	SOT-323		261	
	SOT-523		434	
	DFN1006-3		434	
	SOT-723		434	
Operating Junction Temperature Range		T _J	-55 to +150	°C
Storage Temperature Range		T _{STG}	-55 to +150	°C

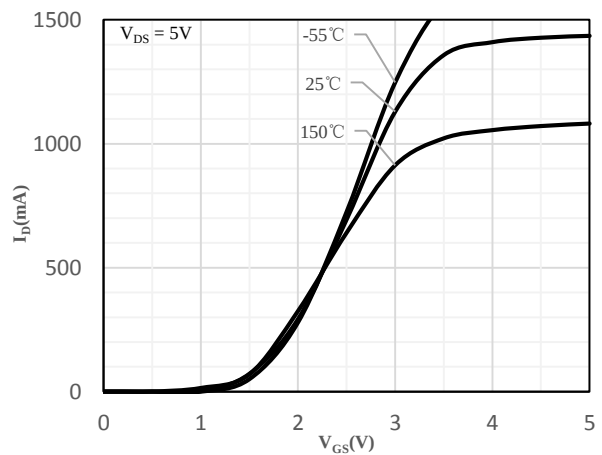
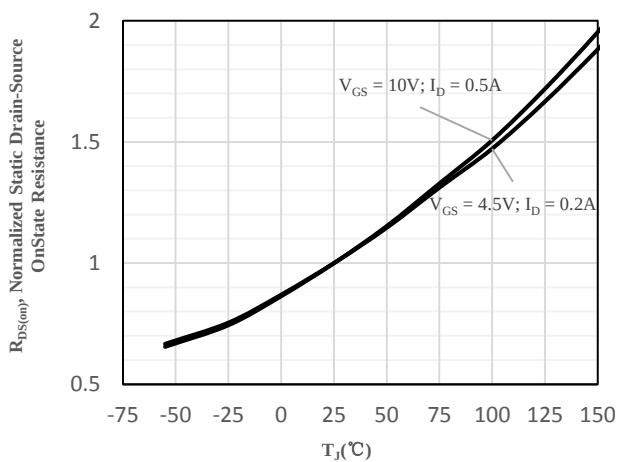
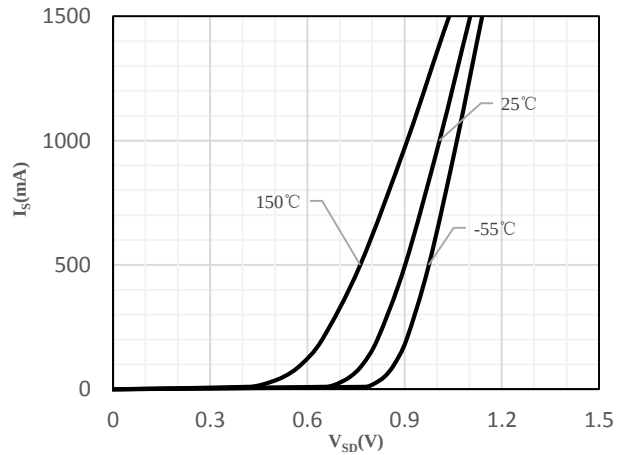
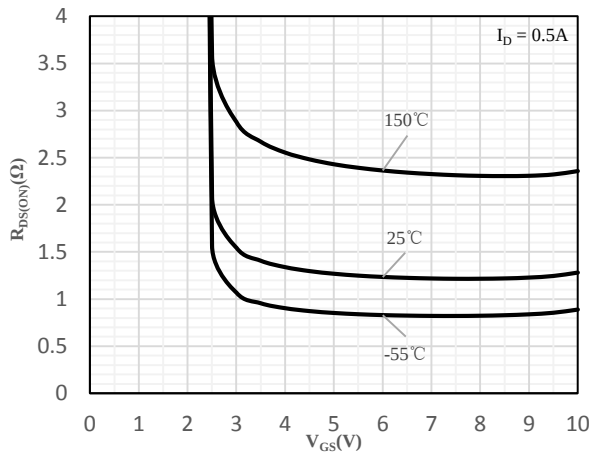
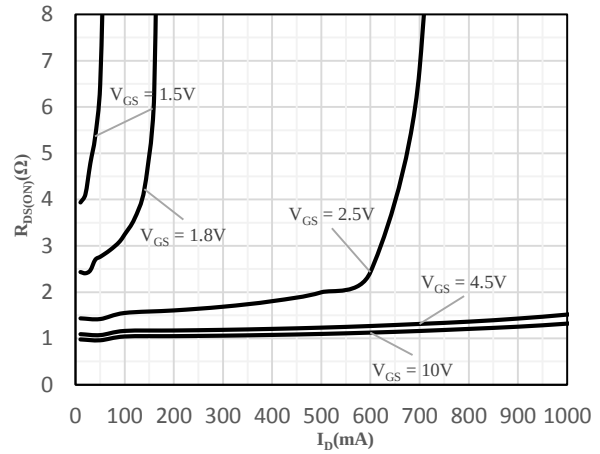
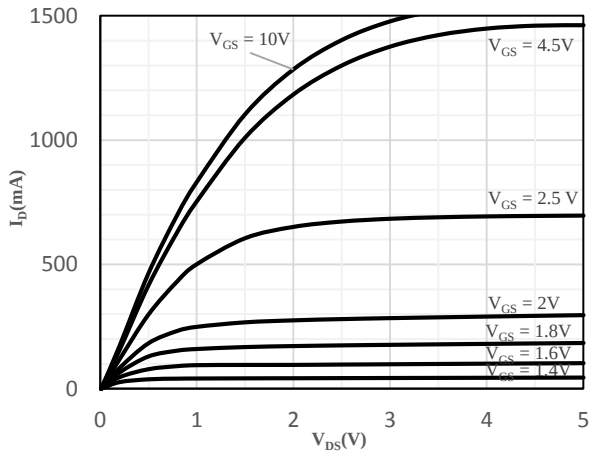
Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	MIN	TYP	MAX	UNIT
OFF Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	50	-	-	V
Δ V _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	I _D = 250μA	-	66	-	mV/°C
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 50V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-body Leakage	V _{GS} = ±20V, V _{DS} = 0V	-	-	±10	μA
ON Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 0.5A	-	1.2	1.5	Ω
		V _{GS} = 4.5V, I _D = 0.2A	-	1.5	2.5	
		V _{GS} = 2.5V, I _D = 0.2A	-	1.6	2.9	
		V _{GS} = 1.8V, I _D = 0.05A	-	2.8	3.2	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250uA	0.5	0.8	1.0	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	34	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 20V f = 1.0MHz	-	41	-	pF
C _{OSS}	Output Capacitance		-	15	-	
C _{RSS}	Reverse Transfer Capacitance		-	4	-	
g _{fs}	Forward Transconductance	V _{DS} = 10V, I _D = 0.2A	-	0.5	-	S
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time *3	V _{DD} = 30V, I _D = 0.2A V _{GS} = 10V, R _G = 25Ω R _L = 150Ω	-	6	-	nS
t _r	Turn-on Rise Time *3		-	5	-	
t _{d(off)}	Turn-Off Delay Time *3		-	25	-	
t _f	Turn-Off Fall Time *3		-	15	-	
Q _G	Total Gate-Charge	V _{DD} = 25V	-	4	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	0.6	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 0.2A	-	0.46	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 0.3A, V _{GS} = 0V	-	0.85	1.2	V
I _S	Diode Continuous Forward Current	T _C = 25°C	-	-	0.3	A

Notes:

- The data tested by surface mounted on a FR-4 board
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)



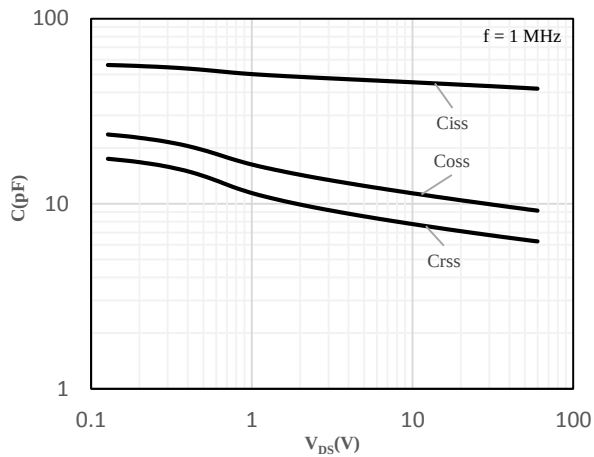


Fig 7 Capacitance Characteristics

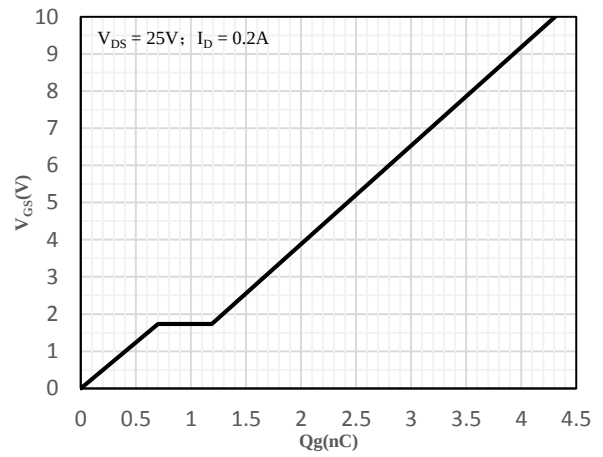


Fig 8 Gate-Charge Characteristics

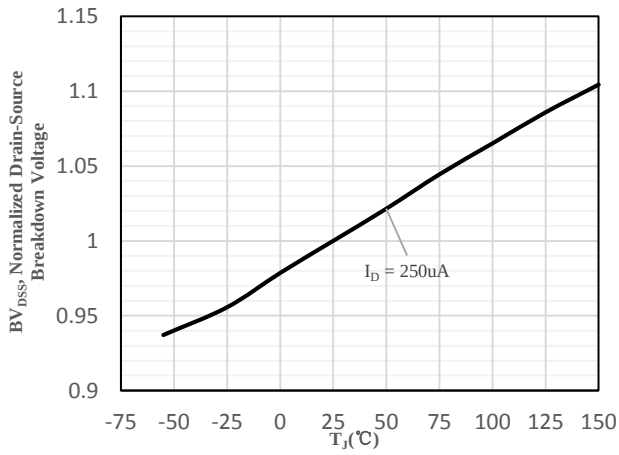


Fig 9 Normalized Breakdown Voltage
vs. Junction Temperature

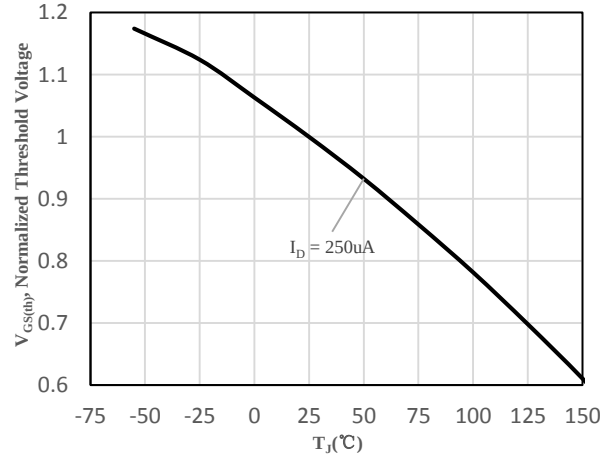


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

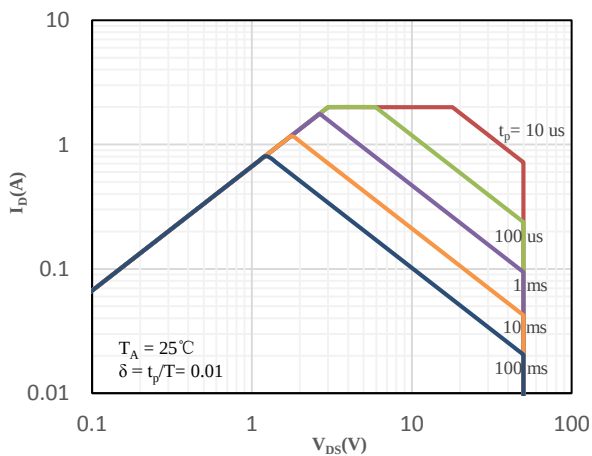


Fig 11 Safe Operation Area

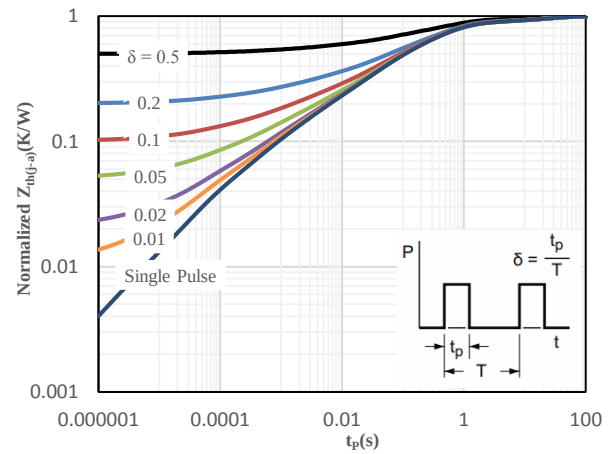
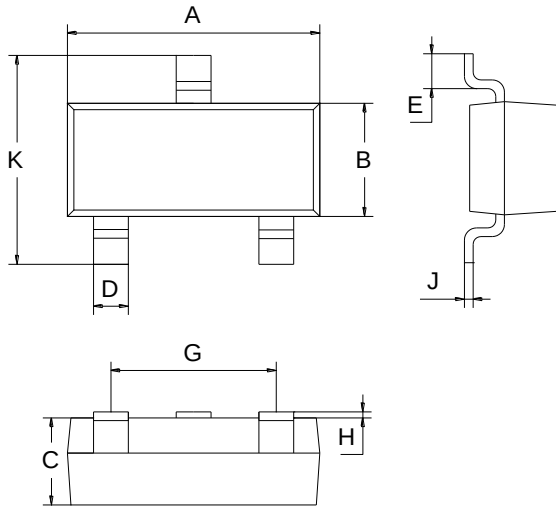
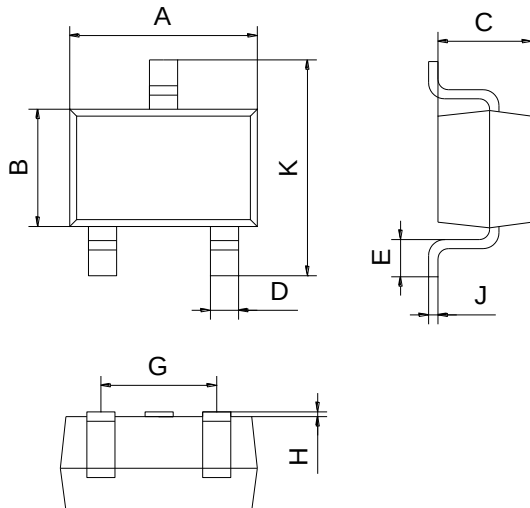


Fig 12 Normalized Maximum transient thermal
impedance

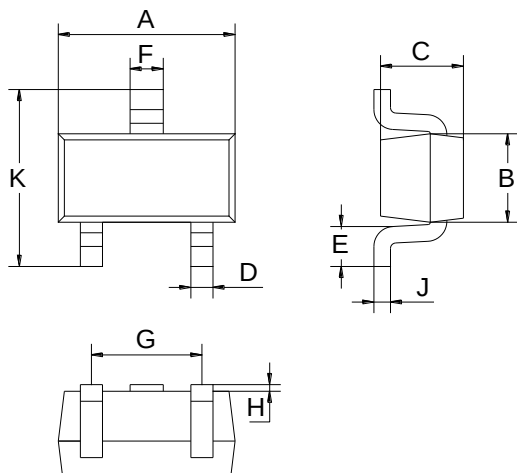
Package Outline Dimensions (Unit: mm)



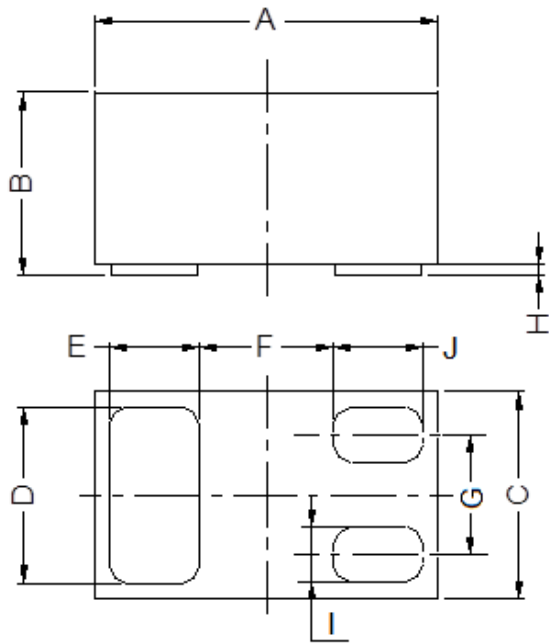
SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60



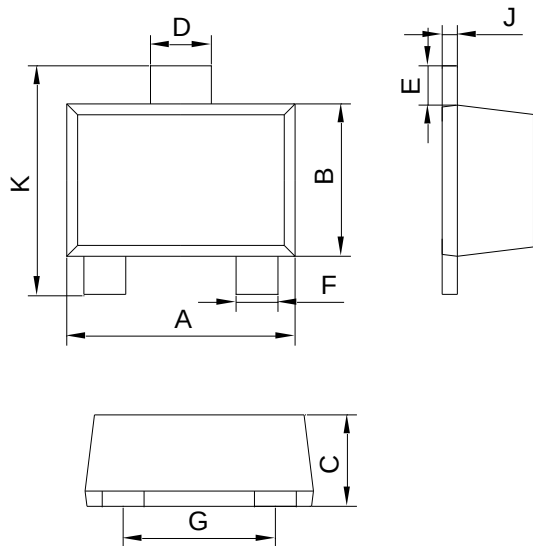
SOT-323		
Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40



SOT-523		
Dimension	Min.	Max.
A	1.50	1.70
B	0.75	0.85
C	0.60	0.80
D	0.15	0.30
E	0.30	0.40
F	0.25	0.40
G	0.90	1.10
H	0.02	0.10
J	0.08	0.18
K	1.45	1.75



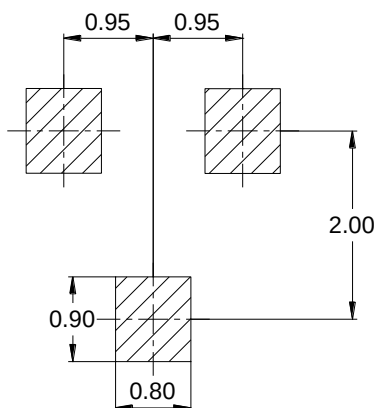
DFN1006-3			
Dimension	Min.	Typ.	Max.
A	0.95	1.00	1.075
B	0.47	0.50	0.53
C	0.55	0.60	0.675
D	0.45	0.50	0.55
E/J	0.20	0.25	0.30
F	-	0.40	-
G	-	0.35	-
H	0	0.03	0.05
I	0.10	0.15	0.20



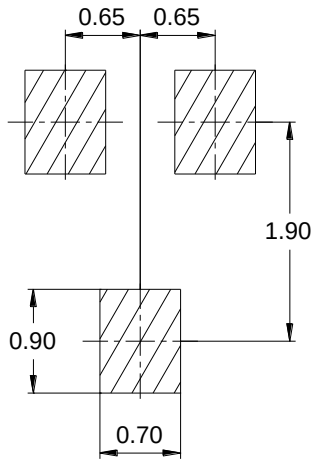
SOT-723		
Dim	Min	Max
A	1.10	1.30
B	0.70	0.90
C	0.40	0.54
D	0.22	0.42
E	0.10	0.30
F	0.12	0.32
G	0.70	0.90
J	0.08	0.15
K	1.10	1.30

Mounting Pad Layout (Unit: mm)

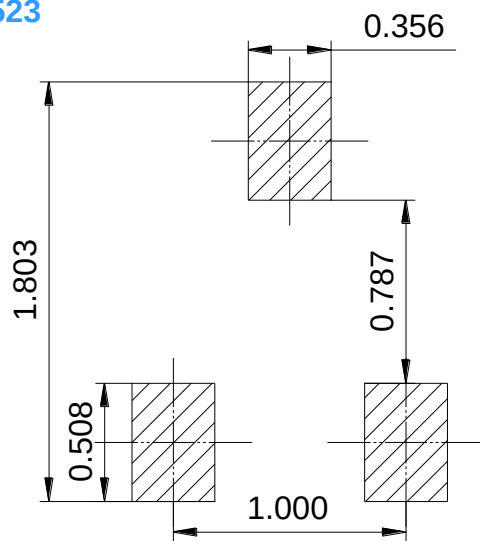
SOT-23



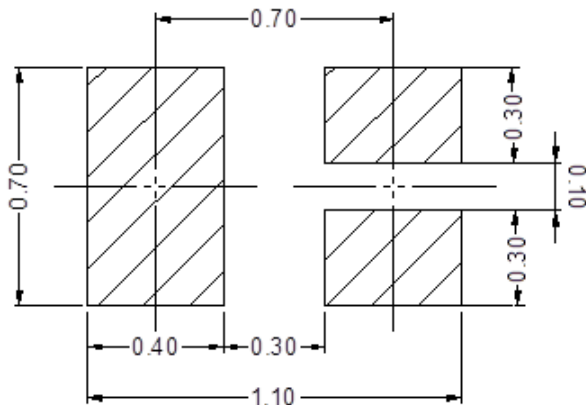
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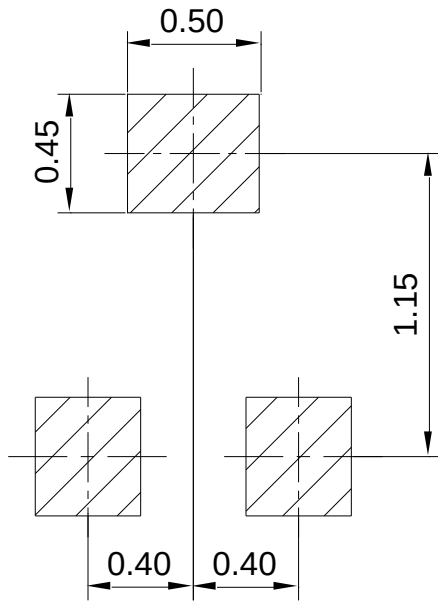
SOT-523



DFN1006-3



SOT-723



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